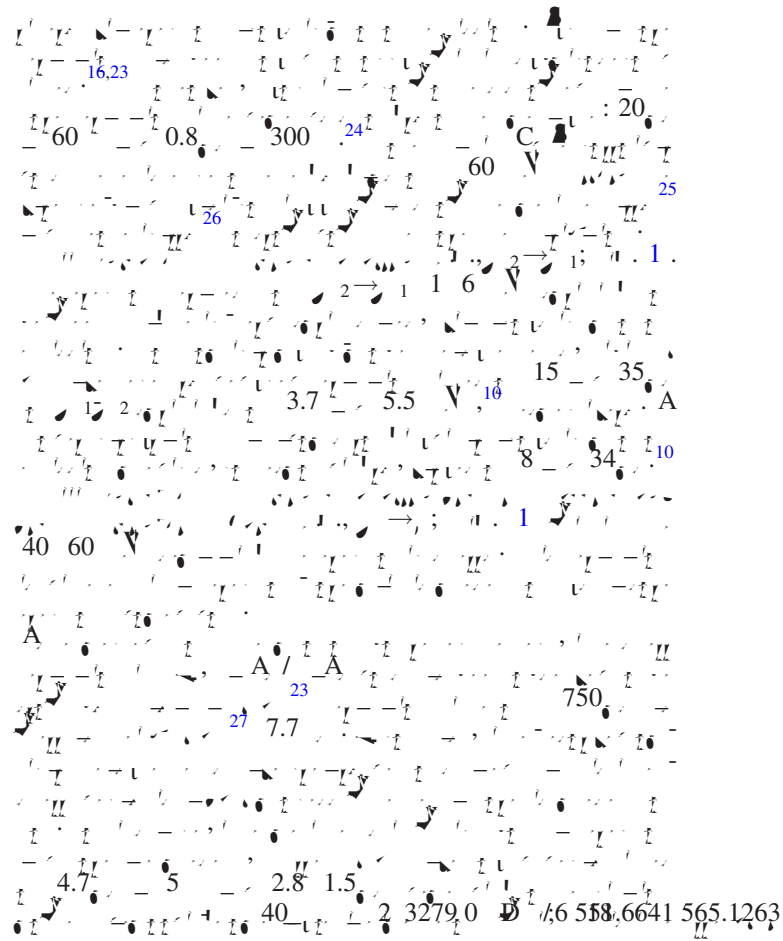
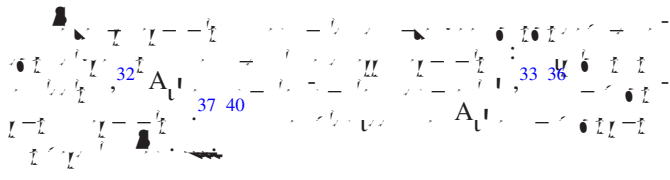


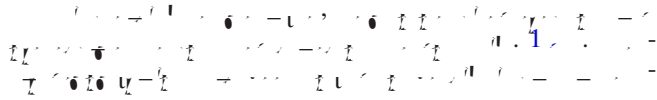
C. Relaxation of excited carriers within the dot

The relaxation of excited carriers within the dot is studied by measuring the time-resolved photoluminescence (TR-PL) decay curves. The decay curves are shown in Fig. 18, 19, 20, and 21. The decay curves are fitted with a single exponential decay function, and the decay time constants are extracted. The decay time constants are shown in Table 1. The decay time constants are in the range of 100 ps to 1 ns. The decay time constants are independent of the excitation intensity, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation wavelength, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation polarization, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot size, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot shape, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot position, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot diameter, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot area, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot volume, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot density, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot flux, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot rate, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot energy, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot power, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot intensity, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot brightness, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot contrast, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot resolution, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot sharpness, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot clarity, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot visibility, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot detectability, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot measurability, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot quantifiability, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot measurability, indicating that the decay is dominated by a single process. The decay time constants are also independent of the excitation spot quantifiability, indicating that the decay is dominated by a single process.





D. Thermal escape of carriers from dot



$R_{,a}^y$ 52
E ψ B
k R A A
k e: 53

$$\frac{1}{2} \left(\frac{1}{2} + \frac{1}{2} \right) = \frac{1}{2} \cdot 1 = \frac{1}{2}$$

...

D. Comparison to other calculations for (In,Ga)As/GaAs dots

... k, p ... ³⁴ ...
... B ... ³⁵ ...
... A ... T ...
... $16 A$... B ... ³⁵ ...
... A ...

⁸E. A. ... A. D. A. ... C. ... E. A. ... 26, 105 2005.

⁹E. A. ... B. ... D. A. C. ... C. ... B 70, 16T305 2004.

¹⁰E. A. ... B. ... D. A. C. ...